RoHS

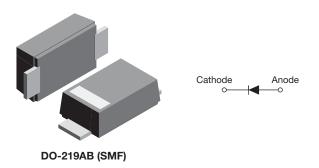
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### **Vishay Semiconductors**

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# Hyperfast Rectifier, 2 A FRED Pt®



PRODUCT SUMMARY				
Package	DO-219AB (SMF)			
I <sub>F(AV)</sub>	2 A			
V <sub>R</sub>	200 V			
V <sub>F</sub> at I <sub>F</sub> (typ. 125 °C)	0.75 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Diode variation	Single die			

#### FEATURES

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="http://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V		
Average rectified forward current	I <sub>F(AV)</sub>	$T_{\rm C} = 150 \ ^{\circ}{\rm C} \ ^{(1)}$	2	٨		
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	50	A		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

#### Note

(1) Device on PCB with 8 mm x 16 mm soldering lands

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-	
Forward voltage	V	I <sub>F</sub> = 2 A	-	0.88	0.95	V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 2 A, T <sub>J</sub> = 125 °C	-	0.75	0.82	
	1	$V_{R} = V_{R}$ rated	-	-	2	
Reverse leakage current I <sub>R</sub>		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1	8	μA
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	8	-	pF

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, \ dI_F/dt = 50 \text{ A}$	õs, V <sub>R</sub> = 30 V	-	24	-	
Reverse recovery time	+	$I_{\rm F} = 0.5 \; {\rm A}, \; I_{\rm R} = 1 \; {\rm A}, \; I_{\rm rr}$	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	25	
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	16	-	ns
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 2 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 160 V	-	22	-	
Deels receiver a current		T <sub>J</sub> = 25 °C		-	2	-	^
Peak recovery current	IRRM	T <sub>J</sub> = 125 °C		-	3	-	A
		T <sub>J</sub> = 25 °C		-	16	-	nC
Reverse recovery charge	verse recovery charge Q <sub>rr</sub>		]	-	30	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	+175	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	15	°C/W	
Thermal resistance, junction to ambient	R <sub>thJA</sub> Device mounted on PCB with 2 mm x 3.5 mm soldering lands		-	-	130	°C/W	
Approvimate weight				0.015		g	
Approximate weight				0.0005		oz.	
Marking device		Case style SMF (DO-219AB)		М	EH		

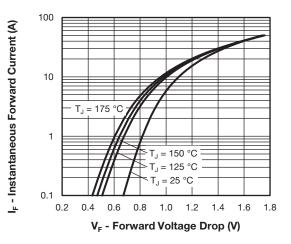


Fig. 1 - Typical Forward Voltage Drop Characteristics

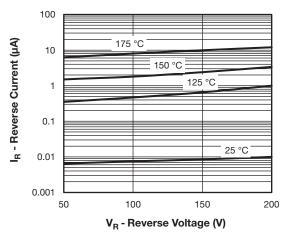


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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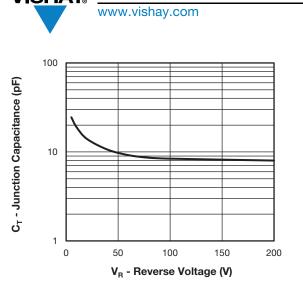


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

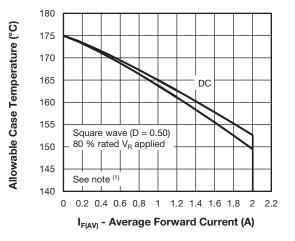


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

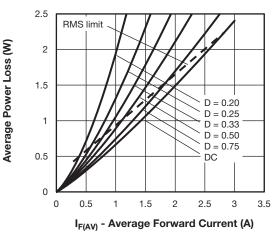


Fig. 5 - Forward Power Loss Characteristics

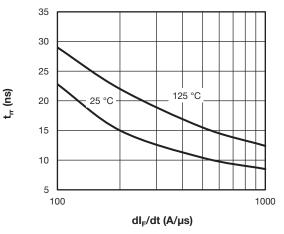


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

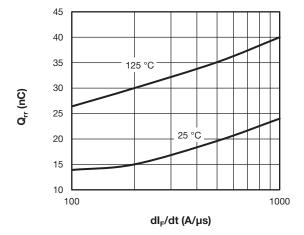


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mbox{Pd} = \mbox{Forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/D) \mbox{ (see fig. 5);} \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 - D); I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{rated } \mbox{V}_{R} \end{array}$ 

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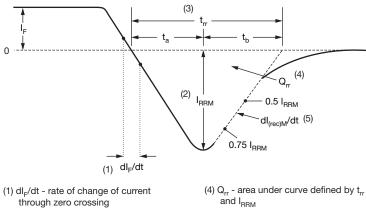
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## VS-2EFH02HM3

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- (2)  $I_{\text{RRM}}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75  $I_{\text{RRM}}$  and 0.50  $I_{\text{RRM}}$  extrapolated to zero current.

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

www.vishay.com

Device code	VS-	2	Е	F	н	02	Н	МЗ
	1	2	3	4	5	6	7	8
	1 2 3	- Cur - Circ	rent rati cuit con	nicondu ing (2 = figuratio	2 A)	oduct		
	4 5	- F = - Pro	single c SMF pa cess typ	ackage oe,				
	6 · 7 · 8 ·	- Voli - H =	tage coo AEC-Q	ast recov de (02 = 101 qua jen-free,	200 V) alified	complia	ant, and	termin

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-2EFH02HM3/I	10 000	10 000	13"diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95572				
Part marking information	www.vishay.com/doc?95618				
Packaging information	www.vishay.com/doc?95577				

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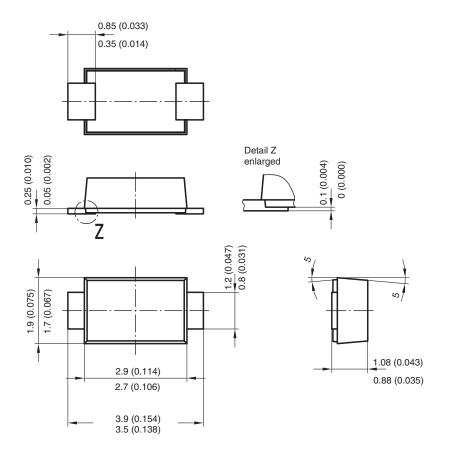
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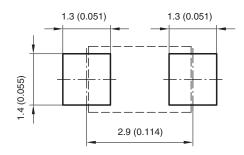
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# DO-219AB (SMF)

#### **DIMENSIONS** in millimeters (inches)



Foot print recommendation:



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